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## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

## FOREIGN PATENT DOCUMENTS

								TRANSLATION	
		DOCUMENT NUMBER	DATE	COUNTRY	NAME	CLASS	SUB CLASS	YES	NO

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

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EXAMINER	DATE CONSIDERED
	8/19/04